Radiation tolerant N-channel Power MOSFETs



A family of radiation tolerant N-channel MOSFETs in plastic packages for LEO missions and (mega) constellations

The Enhanced Commercial Power MOSFETs in plastic packages are designed to meet the requirements for short term, 2-5 year, LEO missions and constellations. The products are single event effect (SEE) tolerant and specified with a LET of 46 MeV·cm²/mg. They can be used in space applications without further radiation tests, like proton tests. They also withstand a Total Ionizing Dose of 30 krad(Si), which supports the targeted mission lifetime of 2-5 years.

The product family offers four different N-channel MOSFETs based on the unique Infineon CoolMOSTM super-junction technology. This makes them ideal for fast switching applications. There are two voltage options, 60 V and 150 V, supporting the most common bus voltages of 28 V and 54 V used in LEO satellites. The $R_{DS(on)}$ values range from 15 m Ω to 60 m Ω .

There are two plastic package options available, the surface mount TO-263 and the through hole TO-247. The TO-263 supports easy assembly and re-flow soldering, while the TO-247 can be used for an optimized cooling concept for higher currents. Both package types have leads plated with matte tin to reduce whisker build.

The radiation tolerant N-channel MOSFETs are qualified according to the automotive standard AEC-Q101 with an operating temperature from -40°C to +125°C.

Key features

Product features

- Optimized for LEO missions and constellations
- Radiation tolerant
 - LET of 46 MeV · cm²/mg
 - TID of 30 krad(Si)
- Automotive qualified according to AEC-Q101 standard
- Two voltage classes: 60 V and 150 V V_{DS} (max)
- RDS(on) (max) @25°C from 15 m Ω to 60 m Ω
- Surface mount and thru hole packages available

Target applications

- Ideally suited for all power related applications including
 - Power condition unit
 - Power distribution unit
 - DC-DC converters

Key benefits

- No component level testing at customer side, as SEE and TID levels are specified on product level
- Commercially attractive due to high volume assembly lines



TO-247 package



TO-263 package



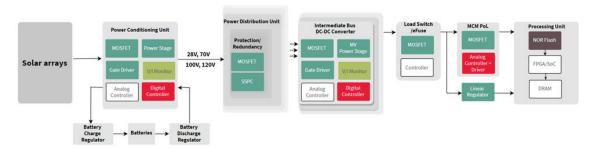




Radiation tolerant N-channel Power MOSFETs

A family of radiation tolerant N-channel MOSFETs in plastic packages for LEO missions and (mega) constellations

Space power architecture



Product table

Product name	Package	Channel	BV _{DSS} (V)	Q _G (nC)	R _{DS(on)} @25°C	I _{DC} @25°C	I _{dpuls} (A)	Power dissipation (W)	Gate voltage	Die size
BUP06CN015E-01	TO-247	N	60	75	15	45	200	390	+/- 20	6
BUP06CN035L-01	TO-263	N		25	35	35	100	150	+/- 20	3
BUP15CN027E-01	TO-247	N	150	75	27	45	180	390	+/- 20	6
BUP15CN060L-01	TO-263	N		25.5	60	23	93	150	+/- 20	3



www.infineon.com/hirel

Published by Infineon Technologies AG Am Campeon 1-15, 85579 Neubiberg, Germany

© 2023 Infineon Technologies AG All rights reserved.

Public

Document number: B119-I1426-V1-7600-NA-EC-P Date: 10/2023

Please note

This Document is for information purposes only and any information given herein shall in no event be regarded as a warranty, guarantee or description of any functionality, conditions and/or quality of our products or any suitability for a particular purpose. With regard to the technical specifications of our products, we kindly ask you to refer to the relevant product data sheets provided by us. Our customers and their technical departments are required to evaluate the suitability of our products for the intended application.

We reserve the right to change this document and/or the information given herein at any time.

Additional information

For further information on technologies, our products, the application of our products, delivery terms and conditions and/orprices, please contacty our nearest Infine on Technologies office (www.infineon.com).

Warning

Due to technical requirements, our products may contain dangerous substances. For information on the types in question, please contact your nearest Infineon Technologies office.

Infineon Technologies Components may only be used in life-support devices or systems with the expressed written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system.

Life support devices or systems are intended to be implanted in the human body, or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.